# MSKSEMI 美森科













**ESD** 

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# MBRS320T3G(MS)

Product specification





#### **FEATURES**

- Small Compact Surface Mountable Package with J-Bend Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop (0.5 V Max @ 3.0 A, TJ = 25°C)
- Excellent Ability to Withstand Reverse Avalanche Energy Transients
- Guard-Ring for Stress Protection
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Mechanical Characteristics**

- Case: Epoxy, Molded, Epoxy Meets UL 94 V-0
- Weight: 217 mg (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Polarity: Polarity Band on Plastic Body Indicates Cathode Lead
- Device Meets MSL 1 Requirements
- ESD Ratings:
   Machine Model = C (> 400 V)
   Human Body Model = 3B (> 8000 V)

#### **Reference News**

PACKAGE OUTLINE	PIN CONFIGURATION	Marking Information
SMC(DO-214AB)		MBRS 320



#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	20	V
Average Rectified Forward Current	lF(AV)	3.0 @ T∟ = 110℃ 4.0 @ T∟ = 105℃	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	IFSM	80	А
Operating Junction Temperature	TJ	- 65 to +150	°C
ISO 7637 Pulse #1 (100 V, 10Ω)		5000	Pulses
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Lead	Rejl	11	°C/W	
	•	•		,

#### **ELECTRICAL CHARACTERISTICS**

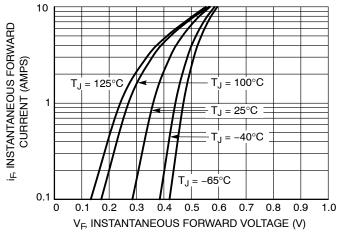
Maximum Instantaneous Forward Voltage (Note 1)			
$(i_F = 3.0 \text{ A}, \text{ TJ} = 25^{\circ}\text{C})$	VF	0.50	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T <sub>J</sub> = 25°C) (Rated dc Voltage, T <sub>J</sub> = 100°C)	İR	2.0 20	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>1.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.



#### TYPICAL ELECTRICAL CHARACTERISTICS



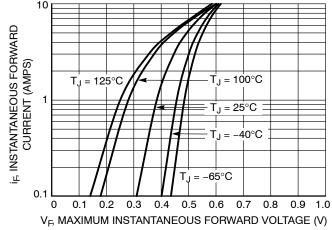
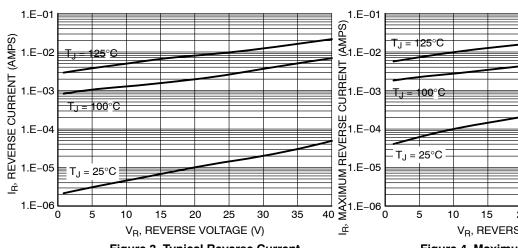


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage



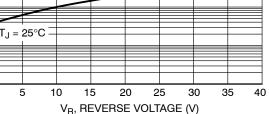
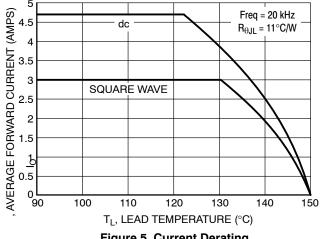


Figure 3. Typical Reverse Current

**Figure 4. Maximum Reverse Current** 



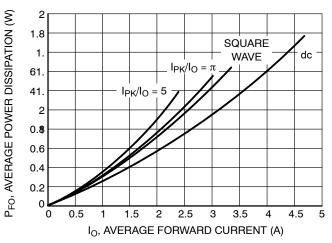


Figure 5. Current Derating

Figure 6. Forward Power Dissipation



## YPICAL ELECTRICAL CHARACTERISTICS (continued)

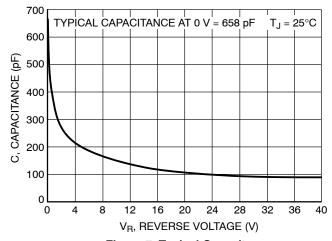
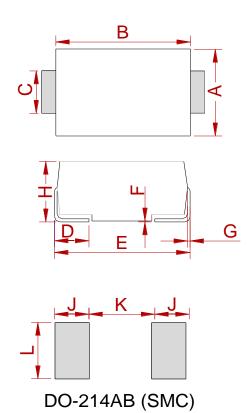


Figure 7. Typical Capacitance



### PACKAGE MECHANICAL DATA



	Dimensions			
Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
Α	5.75	6.25	0.226	0.246
В	6.90	7.40	0.272	0.291
С	2.75	3.25	0.108	0.128
D	0.95	1.52	0.037	0.060
E	7.70	8.20	0.303	0.323
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
Н	2.15	2.62	0.085	0.103
J	2.40		0.094	
K		4.20		0.165
L	3.30		0.130	

#### **REEL SPECIFICATION**

P/N	PKG	QTY
MBRS320T3G(MS)	SMC	3000



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